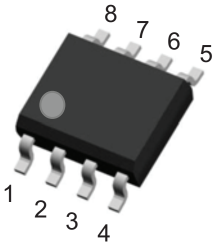
N-Channel Enhancement-Mode MOSFET (30V, 10A)

PRODUCT SUMMARY		
V_{DSS}	I_D	$R_{DS(on)}$ (m-ohm) Max
30V	10A	15 @ V_{GS} = 10V ,ID=10A
		24 @ V_{GS} = 4.5V,ID=5A

Features

- Advanced Trench Process Technology
- High Density Cell Design for Ultra Low On-Resistance
- Lead free product is acquired
- Surface mount Package
- Ordering information：KF4410（Lead（Pb）-free）
  KF4410-G（Lead（Pb）-free and halogen-free）



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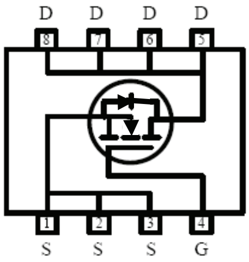

Pin 1 / 2 / 3: Source
Pin 4: Gate
Pin 5 / 6 / 7 / 8: Drain

Absolute Maximum Ratings (T_A=25°C, unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current @T_A=25°C	10	A
	Drain Current @T_A=70°C	8	
I_{DM}	Drain Current (Pulsed) [a]	50	A
P_D	Total Power Dissipation @T_A=25°C	2.5	W
T_j, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +150	°C
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	50	°C/W

a: Repetitive Rating: Pulse width limited by the maximum junction temperature.